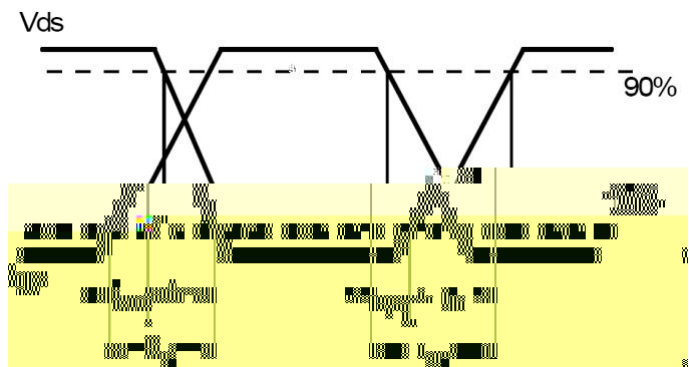
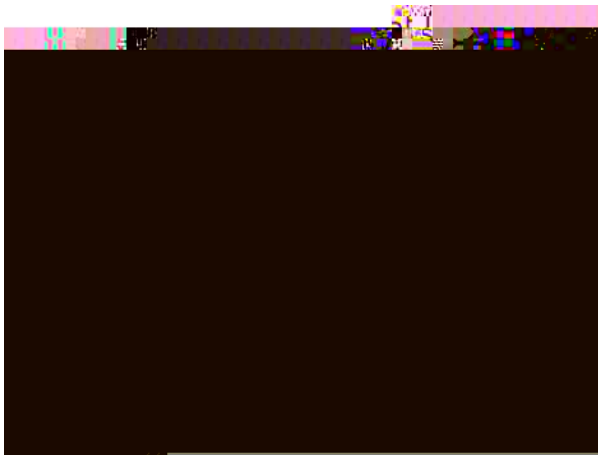
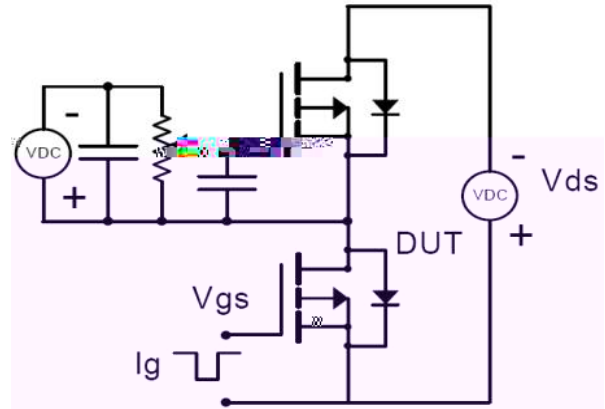
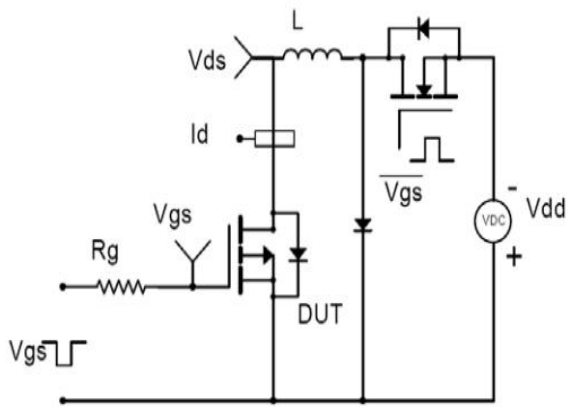


R_{JC}	Junction-to-case	—	3.7	/W
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@ $T_J=25$ unless otherwise specified

$V_{(BR)DSS}$	Drain-to-Source breakdown voltage	-40	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
$R_{DS(on)}$	Static Drain-to-Source on-resistance	—	30	39	m	$V_{GS}=-10V, I_D = -10A$
		—	41	54.5		$V_{GS}=-4.5V, I_D = -8A$
$V_{GS(th)}$	Gate threshold voltage	-1	—	-2.5	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
I_{DSS}	Drain-to-Source leakage current	—	—	-1	μA	$V_{DS} = -40V, V_{GS} = 0V$
I_{GSS}	Gate-to-Source forward leakage	—	—	100	nA	$V_{GS} = 20V$
		—	—	-100		$V_{GS} = -20V$
C_{iss}	Input capacitance	—	1022	—	pF	$V_{GS} = 0V$
C_{oss}	Output capacitance	—	64	—		$V_{DS} = -20V$
C_{rss}	Reverse transfer capacitance	—	49	—		$f = 1MHz$
Q_g	Total gate charge	—	19.5	—	nC	$I_D = -10A,$
Q_{gs}	Gate-to-Source charge	—	2.6	—		$V_{DS}=-20V,$
Q_{gd}	Gate-to-Drain("Miller") charge	—	5.6	—		$V_{GS} = 10V, \omega_{in}$
$t_{d(on)}$	Turn-on delay time	—	14	—	ns	$V_{GS}=-10V, V_{DS} = -20V,$ $R_{GEN}=3, R_L=2$
t_r	Rise time	—	15	—		
$t_{d(off)}$	Turn-Off delay time	—	182	—		
t_f	Fall time	—	85	—		

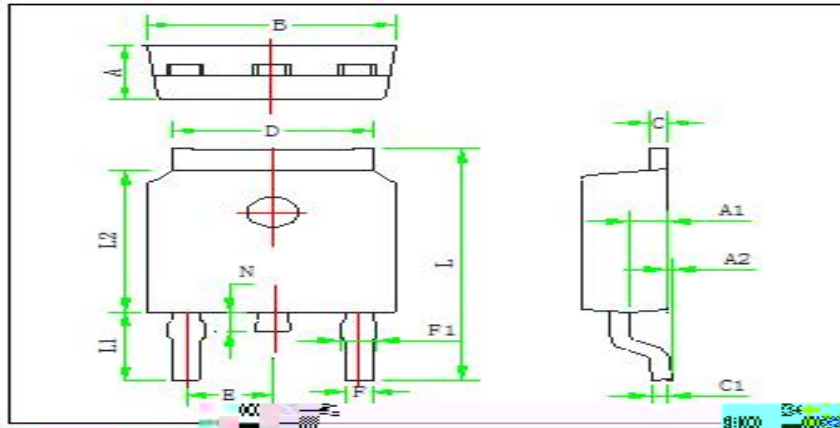
5 E a



Calculated continuous current based on maximum allowable junction temperature.

Repetitive rating; pulse width limited by max. junction temperature.

The power dissipation P_D is based on max. junction temperature, using junction-to-case thermal resistance.



Symbol	Min	Typ	Max
A	2.20	2.50	2.80
A1	0.91	1.01	1.11
A2	0.05	0.15	0.25
B	6.45	6.60	6.75
C	0.45	0.50	0.58
C1	0.45	0.50	0.58
D	5.12	5.32	5.52
E	2.286 TYP		
F	0.66	0.76	0.86
F1	0.66	0.86	1.06
L	9.60	9.90	10.20
L1	2.6	2.8	3.0
L2	5.95	6.10	6.25
N	0.60	0.80	1.00



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